

EFM32LG330 Errata History

F256/F128/F64

This document describes known errata for all revisions of EFM32LG330 devices.





1 Errata History

1.1 Errata Overview

Table 1.1 (p. 2) shows which erratum is applicable for each revision. The device datasheet explains how to identify chip revision, either from package marking or electronically.

In addition to the errata noted below, the errata for the ARM Cortex-M3 r2p1 (www.arm.com) also applies to all revisions of this device.

Table 1.1. Errata Overview

Erratum ID	Rev. E	Rev. D	Rev. C	Rev. B
ADC_E116		х		
ADC_E117		х	Х	х
AES_E101		Х	Х	Х
AES_E102		х	Х	х
BU_E101				х
BU_E102				х
BU_E104				Х
BU_E105	Х	х	х	х
BU_E106		Х		
BURTC_E101		х	х	х
BURTC_E102		Х	Х	Х
CMU_E108				Х
CMU_E110				Х
CMU_E111			Х	Х
CMU_E112		Х		
CMU_E113		х		
CMU_E114	Х	Х	Х	Х

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Erratum ID	Rev. E	Rev. D	Rev. C	Rev. B
CUR_E103			х	
CUR_E104			Х	Х
DAC_E109	Х	Х	Х	Х
DI_E102		х	Х	Х
DMA_E101		Х	Х	Х
EMU_E105				Х
EMU_E107	Х	х	Х	Х
ETM_E101				Х
GPIO_E101				Х
LES_E101				Х
LES_E102				Х
LES_E103		х		
OPA_E101				Х
PCNT_E102	Х	х	Х	Х
PRS_E101		х	Х	Х
RMU_E101	Х			
TIMER_E103	Х	Х	Х	Х
USART_E112		х	Х	Х
USB_E101				Х
USB_E102				х
USB_E103	Х	Х	Х	х
USB_E104	Х	Х	Х	х
USB_E105	Х	Х	Х	х
USB_E106				Х

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Erratum ID	Rev. E	Rev. D	Rev. C	Rev. B
USB_E107			Х	Х
USB_E108			Х	Х
USB_E109	Х	Х	Х	Х
USB_E110	Х	Х	Х	Х

1.2 EFM32LG330 Errata Descriptions

Table 1.2. EFM32LG330 Errata Descriptions

ID	Title/Problem	Effect	Fix/Workaround
ADC_E116	Offset in ADC Temperature Sensor Calibration DataData The ADC temperature sensor calibra- tion value stored in the Device Infor- mation (DI) Page has an offset.	For devices with PROD_REV values of 16 or 17, the ADC0_TEMP_0_READ_1V25 register of the Device Information Page has an offset of 112. Using this value for calculating the absolute temperature gives an approximately 18 degrees too high value. Relative temperature measurements (temperature changes) are not affected by this offset.	For devices with PROD_REV values of 16 or 17, use ADC0_TEMP_0_READ_1V25 - 112 instead of ADC0_TEMP_0_READ_1V25 when calculating the tempera- ture.
ADC_E117	TIMEBASE not wide enough For 48 MHz ADC clock, the ADC_CTRL_TIMEBASE is not wide enough.	For ADC warm-up, the user is required to set the ADC_CTRL_TIMEBASE to the number of ADC clock cycles in 1 μ s. As this register is only 5 bits wide, it does not support frequencies above 32 MHz.	If an ADC clock above 32 MHz is required, the acquis- tion time should be increased to also account for too short warmup-time.
AES_E101	BYTEORDER does not work in combination with DATAS- TART/XORSTART When the BYTEORDER bit in AES_CTRL is set, an encryption or de- cryption should not be started through DATASTART or XORSTART.	If BYTEORDER is used in combination with DATASTART or XORSTART, the AES data and key are interpreted in the wrong order.	Do not use BYTEORDER in combination with DATASTART or XORSTART.
AES_E102	AES_STATUS_RUNNING set one cycle late with BYTEORDER set When the BYTEORDER bit in AES_CTRL is set,	If BYTEORDER is used, it will take one cycle for the AES_STATUS_RUNNING flag to be set. This means that polling this status flag should be postponed at least one cycle after starting encryption/decryption.	If polling the AES_STATUS_RUNNING is preferred, insert a No Operation assembly instruction (NOP()) before starting to poll the status flag.





ID	Title/Problem	Effect	Fix/Workaround
	AES_STATUS_RUNNING is set one cycle late.		
BU_E101	Backup power increased power consumtionAdditional current consumption on BU_VIN approximately 100uA when VDD_DREG is between 0.3 BU_VIN to 0.7 BU_VIN.	Additional current consumption on BU_VIN approximate- ly 100uA when VDD_DREG is between 0.3 BU_VIN to 0.7 BU_VIN.	Avoid having VDD_DREG in between 0.3 BU_VIN to 0.7 BU_VIN.
BU_E102	EM4 GPIO retention in backup mode EM4 GPIO retention not shut off in backup mode.	With GPIO retention enabled, GPIO pins will still drive in backup mode.	Do not use EM4 GPIO retention in combination with backup mode.
BU_E104	EM4 with backup BODs EM4 with backup BODs does not trig- ger reset.	EM4 with backup BODs does not trigger reset.	Avoid using backup BODs when entering EM4.
BU_E105	LFXO missing cycles during IOVDD ramping LFXO missing cycles during IOVDD ramping when used in combination with Backup mode.	When IOVDD is ramped, the dc-level of the XTAL signal changes, resulting in missed LFXO cycles and possible glitches on the LFXO clock.	Set PRESC in BURTC_CTRL to greater then 0 when ramp- ing IOVDD in combination with Backup mode to avoid glitch- es on the LFXO clock.
BU_E106	Current leakage in Backup mode	In Backup mode, when VDD > BU_VIN + 0.7, current will leak from VDD.	To avoid leakage, exit Backup mode before VDD exceeds the voltage where the leakage start by configuring the thresh- old in EMU_BUACT.
BURTC_E101	BURTC LPMODE entry Entering LPMODE with LPCOMP=7 causes counter error.	Counting error occurs if overflow on 7 LSBs happens when entering LPMODE with LPCOMP=7. This results in the counter value being 256 less than it should be after the error. The error accumulates.	Avoid using LPMODE with LPCOMP=7.
BURTC_E102	BURTC_CNT read error Software reads from BURTC_CNT might fail when LPMODE is activated	When LPMODE is active (i.e. BURTC_STATUS_LPMODEACT is high), software reads might result in wrong value being read from BURTC_CNT.	Before reading BURTC_CNT, disable LPMODE and wait for BURTC_STATUS_LPMODEACT to be cleared before read- ing BURTC_CNT.
CMU_E108	LFxCLKEN write First write to LFxCLKEN can be missed.	For devices with PROD_REV < 15, enabling the clock for LFA/LFB after reset and then immediately writing LFA-CLKEN/LFBCLKEN, may cause the write to miss its effect.	For devices with PROD_REV < 15, make sure CMU_SYNCBUSY is not set before writing LFACLKEN/LFB-



ID	Title/Problem	Effect	Fix/Workaround
			CLKEN. Can temporarily switch to HFCORECLKLEDIV2 to speed up clearing synchbusy.
CMU_E110	LFXO phase shift Transients on pin D8 cause LFXO phase shift.	Transients on pin D8 can give a temporary phase shift on LFXO. Frequency is unchanged.	No known workaround.
CMU_E111	LFXO configuration incorrect LFXO configuration incorrect.	For devices with PROD_REV < 15, LFXOBUFCUR in CMU_CTRL is default 0 and LFXOBOOST in CMU_CTRL is default 1. However, these values are incorrect.	On devices with PROD_REV < 15, change LFXOBUFCUR to 1 and LFXOBOOST to 0.
CMU_E112	LFXO boost buffer current setting LFXO boost buffer current must be disabled	LFXO will not work properly with LFXOBUFCUR in CMU_CTRL set.	Do not set LFXOBUFCUR in CMU_CTRL.
CMU_E113	LFXO startup at high temperature LFXO does not start at high tempera- ture with default configuration.	For devices with PROD_REV = 16, LFXO may have startup issues with low capacitance crystals when using the default LFXO configuration.	Make this line of code part of your starup code, typically in the start of main(): *((volatile uint32_t*) 0x400c80C0) = (*((volatile uint32_t*) 0x400c80C0) & \sim (1<<6)) (1<<4);.
CMU_E114	Device not waking up from EM2 when using prescaled non-HFRCO oscillator as HFCLK	If the device is running from any prescaled oscillator other than HFRCO as HFCLK and HFRCO is disabled, the device will not wake up from EM2.	Before entering EM2, clear CMU_CTRL_HFCLKDIV. Alternatively, enable HFRCO by setting CMU_OSCENCMD_HFRCOEN and wait until CMU_STATUS_HFRCORDY is set.
CUR_E103	Increased EM2 current Increased consumption in EM2	Current consumption in EM2 and EM3 has two stable states, the normal state (1200 nA and 900 nA for EM2 and EM3 respectively) and an error state. In the error state the cur- rent consumption in EM2 and EM3 is typically 4.5 uA at 25C (manufacturing test limits is set to 7 uA) but will increase with increased temperature. At 85C the error state EM2 and EM3 current consumption is typically 25 uA. It is unpredictable which state the device will go into on EM2/EM3 entry and it can also change state during operation.	No known workaround.
CUR_E104	Increased current on AVDD2 Increased current on AVDD2 related to VREGO	When VREGO is floating or 0 V, a leakage can appear on AVDD2. This leakage is typically less than 10 uA, but can also rise to around 300 uA.	Make sure VREGO is always defined high when there is power on AVDD2. For bus-powered devices this is always the case, but for devices where the power on VREGO can be lost during operation, e.g. a USB device where the USB phy is powered from VBUS when a master is attached, a 5 MOhm to VDD can help keep VREGO defined.
DAC_E109	DAC output drift over lifetime	When the device is powered and the DAC is disabled, stress on an internal circuit node can cause the output voltage of	Both in the startup initialization code and prior to disabling the DAC in application code, set the OPAnSHORT bit in



ID	Title/Problem	Effect	Fix/Workaround
	The voltage output of the DAC might drift over time.	the DAC to drift over time, and in some cases may violate the $V_{\text{DACOFFSET}}$ specification. If the DAC is always enabled while the device is powered, this condition cannot occur.	DACn_OPACTRL to a '1' for the corresponding DAC(s) used by the application. This will prevent the output voltage drift over time effect.
DI_E102	Flash Page Size The MEM_INFO_PAGE_SIZE value stored in Device Information (DI) Page is incorrect.	For devices with PROD_REV values lower than 18 or in the range [128, 138], the MEM_INFO_PAGE_SIZE register value in the Device Information Page is incorrect.	Use fixed flash page size of 2k bytes.
DMA_E101	EM2 with WFE and DMA WFE does not work for the DMA in EM2.	In EM2, when sleeping with WFE (Wait for Event), an inter- rupt from the DMA will not wake up the system.	Use WFI (Wait for Interrupt) or EM1 instead.
EMU_E105	Debug unavailable during DMA processing from EM2The debugger cannot access the system processing DMA request from EM2.	DMA requests from the LEUART can trigger a DMA opera- tion from EM2. While waiting for the DMA to fetch data from the respective peripheral, the debugger cannot access the system. If such a DMA request is not handled by the DMA controller, the system will keep waiting for it while denying debug access.	Make sure DMA requests triggered from EM2 are handled.
EMU_E107	Interrupts during EM2 entry An interrupt from a peripheral run- ning from the high frequency clock that is received during EM2 entry will cause the EMU to ignore the SLEEP- DEEP-flag.	During EM2 entry, the high frequency clocks that are dis- abled during EM2 will run for some clock cycles after WFI is issued to allow safe shutdown of the peripherals. If an en- abled interrupt is requested from one of these non-EM2 pe- ripherals during this shutdown period, the attempt to enter EM2 will fail, and the device will enter EM1 instead. As a re- sult the pending interrupt will immediately wake the device to EM0.	Before entering EM2, disable all high frequency peripheral in- terrupts in the core.
ETM_E101	ETM Trace Clock ETM Trace Clock needs to be de- layed.	ETM trace clock is out of phase making the data transition occur at the same time as the ETM trace clock transitions.	ETM trace clock needs to be delayed between 10 ns and 1/4 of the trace clock period.
GPIO_E101	GPIO wakeup from EM4 On GPIO wakeup from EM4 all cause bits for high-polarity wakeup pins are set.	All EM4 wakeup cause bits for EM4 wakeup pins with high polarity are set on wakeup.	Use low polarity if possible. For active high, slow changing in- puts, a solution is to sample the inputs on wakeup.
LES_E101	LESENSE and Schmitt trigger Schmitt trigger cannot be disabled on pins used for sensor excitation	When using LESENSE to excite a pin, the pin has to be con- figured in push-pull mode, which also enables the Schmitt trigger. If this pin has an input voltage somewhere in between	Keep the input voltage to pins configured as push-pull out- side the range 0.3*VDD to 0.7*VDD when LESENSE is not interacting with the connected sensor.



ID	Title/Problem	Effect	Fix/Workaround
		0.3*VDD and 0.7*VDD, the Schmitt trigger will consume a considerable ammount of current.	
LES_E102	LESENSE and DAC CH1 configura- tion LESENSE cannot control DAC CH1 if DACCH0CONV in LESENSE_PERCTRL is set to DIS- ABLE.	LESENSE control of DAC CH1 cannot be enabled if DACCH0CONV in LESENSE_PERCTRL is set to DISABLE.	Configure DACCH0CONV in LESENSE_PERCTRL to any- thing but DISABLE, this enables DAC CH1 to be controlled properly. If DAC CH0 is not to be used, set DACCH0OUT in LESENSE_PERCTRL to DISABLE. This will disable LESENSE control of DAC CH0, but still allow LESENSE to control DAC CH1.
LES_E103	AUXHFRCO and LESENSE LESENSE will not work properly at low AUXHFRCO frequencies.	LESENSE will not work properly when used with the AUXH- FRCO running at the 1 or 7 MHz band.	Do not use a AUXHFRCO frequency band of 1 or 7 MHz when used in combination with LESENSE.
OPA_E101	Opamp 2 startup rampup When OPA2 is started the output ram- pup is constant independent of bias setting.	When OPA2 is started the output rampup is constant independent of bias setting.	No known workaround.
PCNT_E102	PCNT Pulse Width Filtering does not work	The PCNT Pulse Width Filter does not work as intended.	Do not use the pulse width filter, i.e. ensure FILT = 0 in PCNTn_CTRL.
PRS_E101	Edge detect on GPIO/ACMP Edge detect on peripherals with asyn- chronous edges might be missed.	When using edge detect in PRS on signals from ACMP, GPIO, RTC, LETIMER, LESENSE, VCMP and BURTC edges can be missed.	Do not use edge detect on ACMP, GPIO, RTC, LETIMER, LESENSE, VCMP and BURTC.
RMU_E101	POR calibration initialization issue Upon initial power-on, some devices may not be able to access flash mem- ory above the 4 kB boundary, or some calibration registers on some devices may not be set to their factory calibra- tion values.	 The list of affected devices can be found in the Knowledge Base (KB) article listed under Fix/Workaround. Some devices are sensitive to the power supply ramp during initial power-on. Specific ramp profiles on these devices can cause an intermittent issue resulting in one of two failure modes (A) or (B): A. Flash memory above the 4 kB boundary is inaccessible. Reads of the flash will return zeros. Write attempts will return an "invalid address" error code in the MSC_STATUS register. Code execution will behave as though the memory above 4 kB was filled with zeros until the device resets itself. 	Additional information including a software workaround is available from the following KB article URL: http://community.silabs.com/t5/32-bit-MCU-Knowledge-Base/ POR-calibration-initialization-issue/ta-p/154716



ID	Title/Problem	Effect	Fix/Workaround
		 B. Some parts of the calibration initialization process do not complete successfully. On USB devices, the USB voltage regulator does not get calibrated. Specific peripheral registers that may not be calibrated are as follows (not all registers apply to all devices): ADC0_CAL, IDAC_CAL, DAC0_BIASPROG, DAC0_OPACTRL, and DAC0_OPAOFFSET. A SYSRESETREQ reset will clear either failure mode, and the device will behave normally until the next power-on event. 	
TIMER_E103	Capture/compare output is unreli- able with RSSCOIST enabled	When RSSCOIST is set and PRESC > 0 in TIMERn_CTRL, the capture/compare output value is not reliable.	Do not use a prescaled clock, i.e. ensure PRESC = 0 in TIMERn_CTRL when RSSCOIST is enabled.
	The TIMER capture/compare output is unreliable when RSSCOIST is enabled and the clock is prescaled.		
USART_E112	USART AUTOTX continues to trans- mit even with full RX buffer	When AUTOTX in USARTn_CTRL or AUTOTXEN in USARTn_TRIGCTRL is set, the USART will continue to transmit data even after the RX buffer is full. This may cause	No known workaround.
	USART AUTOTX continues to transmit even with full RX buffer.	the RX buffer to overflow if the data is not read out in time.	
USB_E101	USB DMA transfers with prescaled HFCLK	USB DMA transfers to flash may fail when prescaling HF-CLK.	Do not prescale HFCLK when using USB-DMA transfers to read from flash.
	USB DMA transfers to flash fail when prescaling HFCLK.		
USB_E102	USB datalines	USB datalines rise and fall time are slightly outside specifica- tion under worst case conditions. They may fail USB certifica-	No known workaround.
	USB datalines rise and fall time are slightly outside specification.	tion eye test depending on PCB layout.	
USB_E103	HNP Sequence fails if A-Device con- nects after 3.4ms	The B-Device core only waits for up to 3.4ms before sig- nalling HNP fail and reverting back to Peripheral mode. Therefore, the HNP sequence fails if the A-Device connects after 3.4ms.	No known workaround.
USB_E104	USB A-Device delays the HNP switch back process	The A-Device core delays the HNP switch back process. As per the USB-OTG 2.0 specification, the B-Device on the oth- er side of the USB pipe either should wait for disconnect from the A-Device or should switch to Peripheral mode and wait	No known workaround.



ID	Title/Problem	Effect	Fix/Workaround
	The D+ line disconnects after 200 ms, delaying the HNP switch back process.	for the A-Device to issue a USB reset. Hence, there is no sig- nificant impact on actual operation.	
USB_E105	B-Device as Host driving K-J pairs during reset The A-Device misinterprets the K-J pairs as Suspend after switching to High Speed mode.	If the B-Device as Host on the other side of the USB pipe drives K-J pairs for more than 200 ms during USB reset, the A-Device core exits peripheral state, causing the HNP pro- cess to fail. There is no significant impact since normally the host drives USB reset for a shorter time than 200 ms.	No known workaround.
USB_E106	USB interrupts USB interrupts have changed from be- ing level triggered to edge triggered.	USB inteerrupts are now trigggered by signal edge rather then signal level.	Make sure to handle edge triggered interrupt, rather then sig- nal level interrupts.
USB_E107	Entry to EM4 causes temporary leakage from VREGO Entry to EM4 causes temporary leak- age from VREGO.	On transition from EM0 to EM4 a current leakage from VREGO of up to 1 mA lasting a few seconds can occur.	No known workaround.
USB_E108	Floating DM/DP pins cause leakage when USB is disabled Floating DM/DP pins cause leakage when USB is disabled.	When the USB_DM or USB_DP pins are floating while the USB PHY is disabled, a current in the order of a couple hundred uA may leak from USB_VREGO to VSS. This will not be an issue if there is no voltage applied to USB_VREGO, either externally or through the USB regulator.	If there is no intention to use the USB module, e.g. the USB PHY is disabled, but there is still a voltage on USB_VREGO, make sure the USB_DM and USB_DP pins are defined. This can be done using GPIO or by defining them externally.
USB_E109	Missing USB_GINTSTS.SESSREQINT Interrupt with USB_PCGCCTL.STOPPCLK = 1 A Host-initiated Suspend, followed by a Host Disconnect and Host Connect will not result in a SessReq interrupt.	When USB_PCGCCTL.STOPPCLK is set and the device is acting as a B-peripheral, a Host-initated Suspend, followed by a Host Disconnect and Host Connect will not result in a SessReq interrupt.	If this is an expected use-case, USB_PCGCCTL.STOPPCLK should not be set. USB_PCGCCTL.GATEHCLK can still be used to save power.
USB_E110	Unexpected USB_HCx_INT.CHHLTD interrupt In some cases the USB_HCx_INT.CHHLTD interrupt might be incorrectly set.	In some cases, an unexpected USB_HCx_INT.CHHLTD interrupt might be received from another endpoint that does not have the USB_HCx_CHAR.CHDIS, USB_HCx_INT.XACTERR, USB_HCx_INT.BBLERR, USB_HCx_INT.DATATGLERR or USB_HCx_INT.XFERCOMPL interrupts enabled.	If such an interrupt is received, the application must re- enable the channel for which it received the unexpected USB_HCx_INT.CHHLTD interrupt.

2 Revision History

2.1 Revision 1.10

October 5th, 2015

Added TIMER_E103.

Added PCNT_E102.

Added RMU_E101.

Added DAC_E109.

Added EMU_E107.

Removed MSC_E101.

2.2 Revision 0.50

June 13th, 2014

Updated to product revision E.

2.3 Revision 0.40

August 21st, 2013

Added ADC_E117.

Added AES_E102.

Added USB_E109.

Added USB_E110.

Updated disclaimer, trademark and contact information.

2.4 Revision 0.30

July 30th, 2013

Added AES_E101.

Added BURTC_E102.

Added CMU_E114.

Added DMA_E101.

Updated errata naming convention.

2.5 Revision 0.20

June 5th, 2012

Added ADC1.

Added DI1.

2.6 Revision 0.10

April 24th, 2012

Initial preliminary release.

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B Contact Information

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